

AMENDMENTS TO THE CLAIMS

Following is a listing of all claims in the present application, which listing supersedes all previously presented claims:

Listing of Claims:

1-66. (Canceled)

67. (Currently Amended) A [[The]] thin film semiconductor device, comprising
as claimed in claim 1, wherein the semiconductor chip comprises:

a flexible substrate;

an active semiconductor element formed on the flexible substrate, the active
semiconductor element including a source, a drain, and a channel;

an insulating region formed on the active semiconductor element;

a gate electrode formed on the insulating region;

a second insulating region formed on the gate electrode;

a source electrode formed on the second insulating region and connected with the
source;

a drain electrode formed on the second insulating region and connected with the drain,
and

a wherein the protective cap [[is]] formed on the second insulating region and on the
source and drain electrodes, and between the active semiconductor element and the flexible
substrate,

wherein the protective cap is formed of any one of an ultraviolet curing resin, an X-ray
curing material, an electronic beam curing material, and an ion beam curing material.

68. (Previously Presented) The thin film semiconductor device as claimed in claim 67, further comprising:

- a third insulating region formed on the protective cap;
- a first pixel electrode formed on the third insulating region;
- a pixel element formed on the first pixel electrode; and
- a second pixel electrode formed on the pixel element.

69. (Currently Amended) A semiconductor device, comprising:
a flexible substrate;
a semiconductor chip formed on the flexible substrate; and
a protective material surrounding the semiconductor chip, wherein the protective material is on a surface of the semiconductor chip that is adjacent to the flexible substrate and is on a surface of the semiconductor chip that is opposite the flexible substrate

wherein the semiconductor chip comprises:

an active semiconductor element formed on a region of the protective material, the active semiconductor element including a source, a drain, and a channel, wherein a portion of the region of the protective material extends laterally beyond the active semiconductor element;

an insulating region formed on the active semiconductor element;

a gate electrode formed on the insulating region;

a second insulating region formed on the gate electrode;

a source electrode formed on the second insulating region and connected with the source; and

a drain electrode formed on the second insulating region and connected with the drain.

wherein a second region of the protective material is formed on the second insulating region, and on the source and drain electrodes, and on the portion of the region of the protective material that extends laterally beyond the active semiconductor element, and wherein the protective material is formed of any one of an ultraviolet curing resin, an X-ray curing material, an electronic beam curing material, and an ion beam curing material.

70. (Previously Presented) The semiconductor device as claimed in claim 69, wherein the tensile strength of the protective material is greater than about 30 GPa.

71. (Canceled).

72. (Currently Amended) A thin film transistor liquid crystal display, comprising:
a driving unit formed on a flexible substrate, the driving unit including a capping layer that forms an upper surface of the driving unit and contacts the flexible substrate;
a pixel unit; and
an insulating layer disposed between the driving unit and the capping layer, wherein:
the pixel unit is connected to the driving unit by a conductive element that passes through the insulating layer and the capping layer, protective cap, and
the capping layer has a tensile strength higher than about 30 GPa and a hardness higher than about 200 Brinell, and
the capping layer is formed of any one of an ultraviolet curing resin, an X-ray curing material, an electronic beam curing material, and an ion beam curing material.

73. (Currently Amended) A semiconductor device, comprising:

- a flexible substrate;
- a semiconductor chip formed on the flexible substrate; and
- a protective material surrounding the semiconductor chip, wherein the protective material is formed on an upper surface and a side surface of the semiconductor chip and between the semiconductor chip and the flexible substrate,

wherein the protective material is formed of any one of an ultraviolet curing resin, an X-ray curing material, an electronic beam curing material, and an ion beam curing material.